



Features

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Temperature range 55 °C to 110 °C

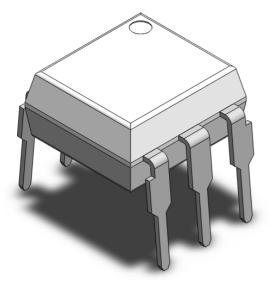
Applications

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface
- AC Line Monitor

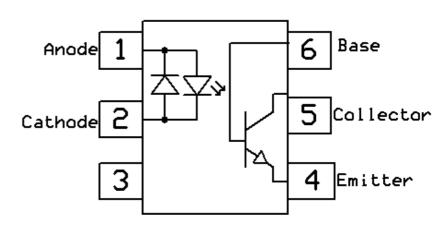
Description

The H11AAX series consists of a phototransistor optically coupled to a gallium arsenide Infrared-emitting diode in a 6-lead DIP package with bending options.

Package Outline



Schematic



Note: Different bending options available. See package dimension.





Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage	5000	V _{RMS}	
Topr	Operating temperature	-55 ~ +110	°C	
Тѕтс	Storage temperature	-55 ~ +125	°C	
TsoL	Soldering temperature	260	°C	
Emitter				
l _F	Forward current	60	mA	
I _F (TRANS)	Peak transient current (≤1µs P.W,300pps)	1	Α	
V_{R}	Reverse voltage	6	V	
P _D	Power dissipation	100	mW	
Detector				
PD	Power dissipation	150	mW	
Bvceo	Collector-Emitter Breakdown Voltage	80	V	
B _{VCBO}	Collector-Base Breakdown Voltage	80	V	
B _{VECO}	Emitter-Collector Breakdown Voltage	7 V		
Вуево	Emitter-Base Breakdown Voltage	7	V	



Electrical Characteristics $T_A = 25$ °C (unless otherwise specified)

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I _F =10mA		1.2	1.4	V	
C _{IN}	Input Capacitance	f= 1kHz	-	45	-	pF	

Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
Bvceo	Collector-Emitter Breakdown	Ic= 100μA	80	-	-	V	
Bveco	Emitter-Collector Breakdown	I _E = 1mA	7	-	-	V	
Вусво	Collector-Base Breakdown	I _C = 100μA	80	-	-	V	
B _{VEBO}	Emitter-Base Breakdown	I _E = 100μA	7	-	-	V	
ICEO	Collector-Emitter Dark Current	V _{CE} = 10V, I _F =0mA	-	-	45	nA	
I _{CBO}	Collector-Base Dark Current	V _{CB} = 10V, I _F =0mA	-	-	20	nA	

Transfer Characteristics

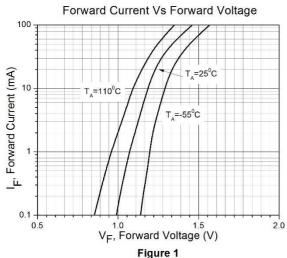
Symbol	P	arameters	Test Conditions	Min	Тур	Max	Units	Notes
	Current Transfer Ratio	H11AA1	I _F = ±10mA, V _{CE} = 10V	20	-	-	- %	
CTR		H11AA2		10	-	-		
CIK		H11AA3		50		-		
		H11AA4		100	ı	•		
V _{CE(SAT)}	Collector- E	mitter Saturation	I _F = ±10mA, I _C = 0.5mA	_	_	0.4	V	
V CE(SAT)	Voltage		IF= ±TOINA, IC= 0.5INA		-	0.4	V	
	Symmetric (CTR	I _F = ±10mA, V _{CE} = 10V	0.5		2.0		
R _{IO}	Isolation Re	sistance	V _{IO} = 500V _{DC}	1x10 ¹¹			Ω	
Cıo	Isolation Ca	pacitance	f= 1Mhz		0.25		pF	

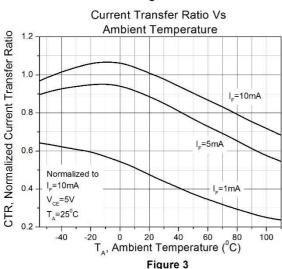
Switching Characteristics

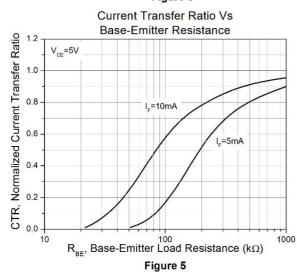
Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
Ton	Turn On Time		•	-	9.8		
T _{OFF}	Turn Off Time	I _F = 10mA, V _{CE} = 10V, R _L =	-	-	9.8		
tr	Rise Time	100Ω	-	-	9.8	μS	
t _f	Fall Time		-	-	9.8		

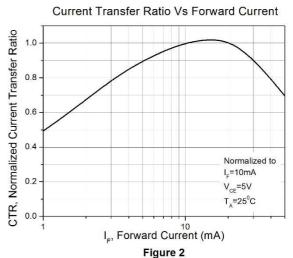


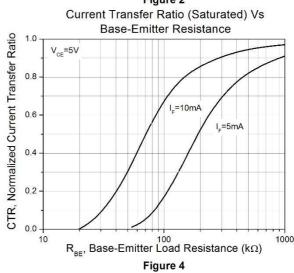
Typical Characteristic Curves

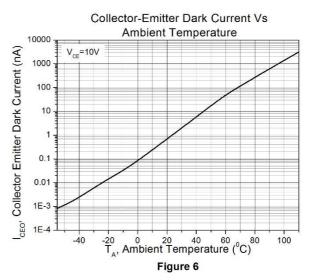






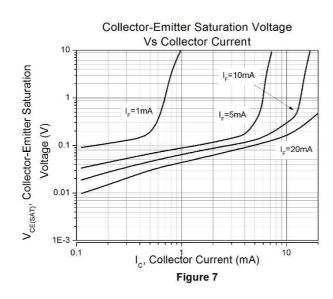


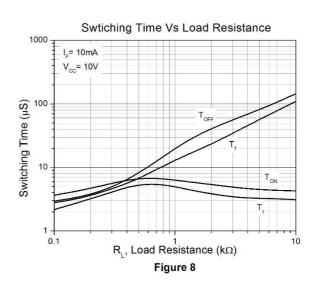


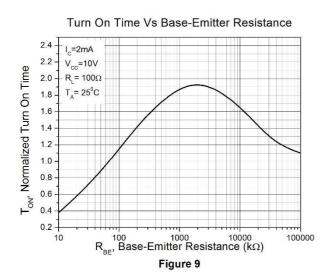


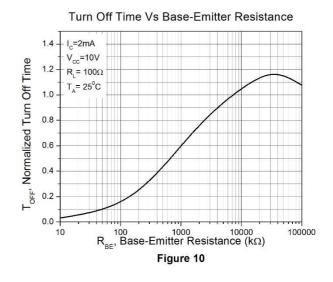








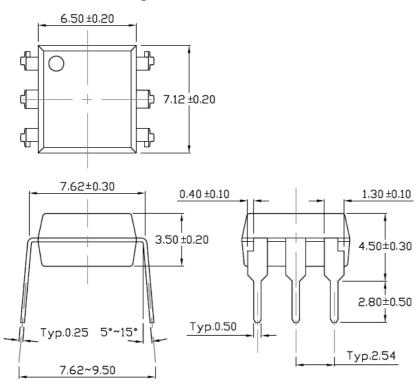




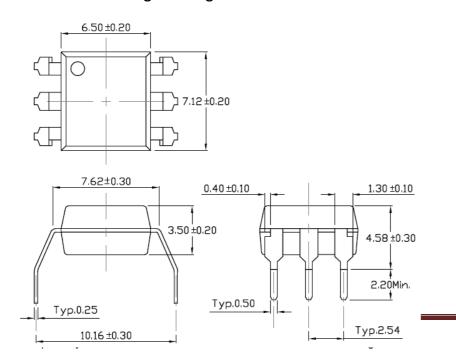


Package Dimension Dimensions in mm unless otherwise stated

Standard DIP - Through Hole

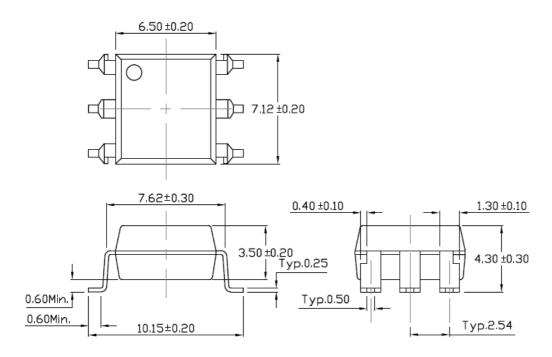


Wide Lead Forming – Through Hole

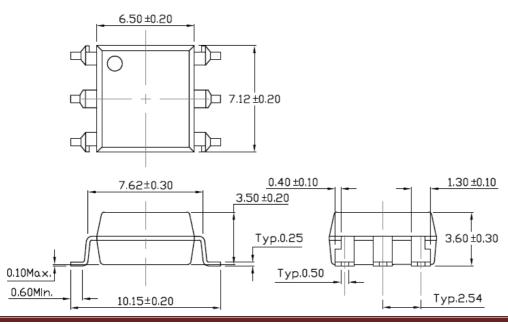




Surface Mount Forming

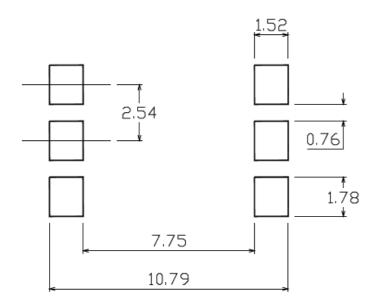


Surface Mount Forming (Low Profile)

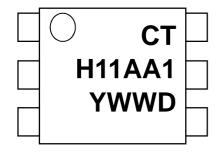




Recommended Solder Mask Dimensions in mm unless otherwise stated



Marking Information



Note:

CT: Logo

H11AA1: Product Number

Y : Fiscal Year WW : Work Week

D : Production Code



Ordering Information

H11AAX(Y)(Z)

X = (1, 2, 3, 4)

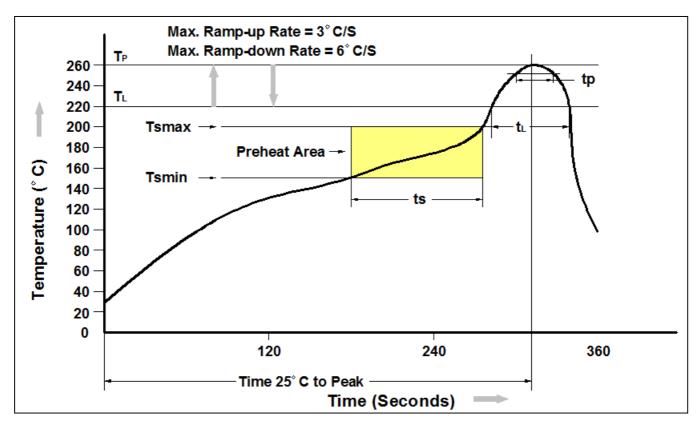
Y = Lead form option (S, S1, M or none)

Z = Tape and reel option (TA, TB or none)

Option Description		Quantity			
None	None Standard 6 Pin Dip				
M	M Wide Lead Forming				
S(TA)	S(TA) Surface Mount Lead Forming – With Option A Taping				
S(TB)	S(TB) Surface Mount Lead Forming – With Option B Taping				
S1(TA)	S1(TA) Surface Mount Lead Forming(Low Profile) – With Option A Taping				
S1(TB)	S1(TB) Surface Mount Lead Forming(Low Profile) – With Option B Taping				



Reflow Profile







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or (c)
whose
failure to
perform
when
properly

used in

Pb-Free Assembly Profile				
150°C				
200°C				
60-120 seconds				
3°C/second max.				
217°C				
60 – 150 seconds				
260°C +0°C / -5°C				
30 seconds				
6°C/second max				
8 minutes max.				

the life
support
device or
system, or to
affect its
safety or
effectiveness.

accordance with instruction for use provided in the labelling, can be reasonably expected to result in significant injury to the user.



H11AAX

6Pin Phototransistor Coupler